L Number	Hits	Search Text	DB	Time stamp
149	90140	low adj voltage	LICDAT:	0004/00/08
149	90140	low adj voitage	USPAT;	2004/09/08
150	140205	1.2-1 32 1	US-PGPUB	18:54
150	140305	high adj voltage	USPAT;	2004/09/08
			US-PGPUB	18:59
151	79147	silicon adj nitride	USPAT;	2004/09/08
			US-PGPUB	18:59
152	5606	"Si.sub.3N.sub.4"	USPAT;	2004/09/08
			US-PGPUB	19:00
153	956	Si3N4	USPAT;	2004/09/08
			US-PGPUB	19:00
154	345	"Si.sub.xN.sub.y"	USPAT;	2004/09/08
			US-PGPUB	19:00
155	96	SixNy	USPAT;	2004/09/08
			US-PGPUB	19:00
156	136137	silicon adj \$2oxide	USPAT;	2004/09/08
			US-PGPUB	19:01
157	133914	"SiO.sub.2"	USPAT;	2004/09/08
			US-PGPUB	19:01
158	6893	SiO2	USPAT;	2004/09/08
			US-PGPUB	19:01
159	9915	gate adj dielectric	USPAT;	2004/09/08
			US-PGPUB	19:01
160	28282	gate adj insulat\$3	USPAT;	2004/09/08
			US-PGPUB	19:02
161	558	(low adj voltage) and (high adj voltage) and	USPAT;	2004/09/08
		(((silicon adj nitride) or "Si.sub.3N.sub.4" or Si3N4	US-PGPUB	19:16
		or "Si.sub.xN.sub.y" or SixNy) same ((gate adj		
		dielectric) or (gate adj insulat\$3))) and (((silicon adj		
		\$20xide) or "SiO.sub.2" or SiO2) same ((gate adj		
		dielectric) or (gate adj insulat\$3)))		
162	2898	dual adj gate	USPAT;	2004/09/08
			US-PGPUB	19:16
163	326	(dual adj gate) and (((silicon adj nitride) or	USPAT;	2004/09/08
ļ		"Si.sub.3N.sub.4" or Si3N4 or "Si.sub.xN.sub.y" or	US-PGPUB	19:17
		SixNy) same ((gate adj dielectric) or (gate adj		
		insulat\$3))) and (((silicon adj \$2oxide) or		
		"SiO.sub.2" or SiO2) same ((gate adj dielectric) or		
		(gate adj insulat\$3)))		

L	Hits	Search Text	DB	Time stamp
Number				
-	6	(("6294421") or ("6110842") or ("6030862") or	USPAT;	2004/09/08
		("5960289") or ("6262455") or ("6037224")).PN.	US-PGPUB	15:23
-	42	dual adj2 oxide adj thickness	USPAT;	2004/09/08
			US-PGPUB	15:24
-	1	dual adj2 insulat\$3 adj thickness	USPAT;	2004/09/08
			US-PGPUB	15:24
-	11	dual adj2 dielectric adj thickness	USPAT;	2004/09/08
			US-PGPUB	15:25
-	2	multiple adj2 dielectric adj thickness	USPAT;	2004/09/08
			US-PGPUB	15:25
-	1	multiple adj2 insulat\$3 adj thickness	USPAT;	2004/09/08
			US-PGPUB	15:25
-	29	multiple adj2 oxide adj thickness	USPAT;	2004/09/08
			US-PGPUB	15:26
-	2778	(clean\$3 or remov\$3 or etch\$3) near3 (native adj	USPAT;	2004/09/08
	_	oxide)	US-PGPUB	15:28
-	0	((dual adj2 oxide adj thickness) or (dual adj2	USPAT;	2004/09/08
		insulat\$3 adj thickness) or (dual adj2 dielectric adj	US-PGPUB	15:28
		thickness) or (multiple adj2 dielectric adj		
		thickness) or (multiple adj2 insulat\$3 adj		
		thickness) or (multiple adj2 oxide adj thickness))		
		and ((clean\$3 or remov\$3 or etch\$3) near3 (native		
	0077070	adj oxide))		
-	2277279	clean\$3 or remov\$3 or etch\$3	USPAT;	2004/09/08
	77	//desal adio anida adi 45:-1	US-PGPUB	15:28
-	77	((dual adj2 oxide adj thickness) or (dual adj2	USPAT;	2004/09/08
		insulat\$3 adj thickness) or (dual adj2 dielectric adj	US-PGPUB	15:29
		thickness) or (multiple adj2 dielectric adj		
		thickness) or (multiple adj2 insulat\$3 adj		
		thickness) or (multiple adj2 oxide adj thickness))		
		and (clean\$3 or remov\$3 or etch\$3)	L	